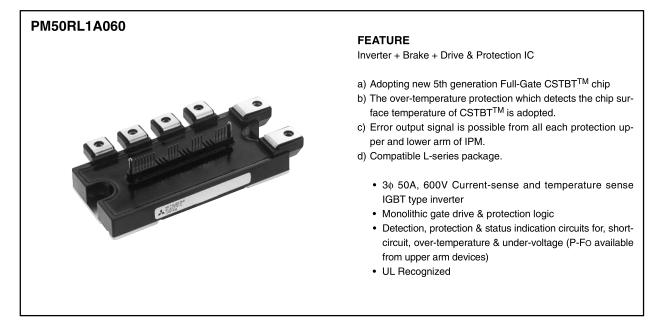
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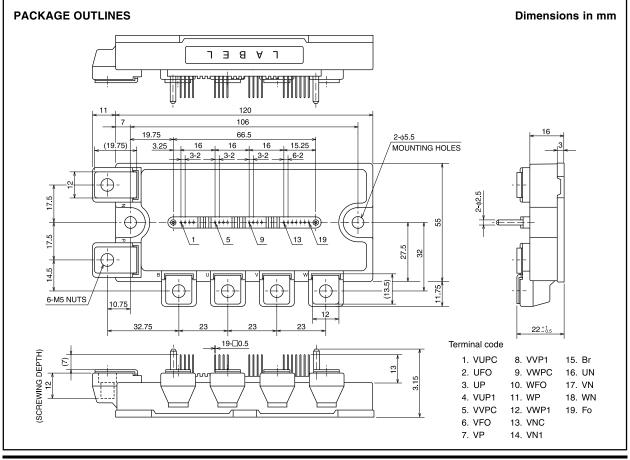
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FLAT-BASE TYPE INSULATED PACKAGE



APPLICATION

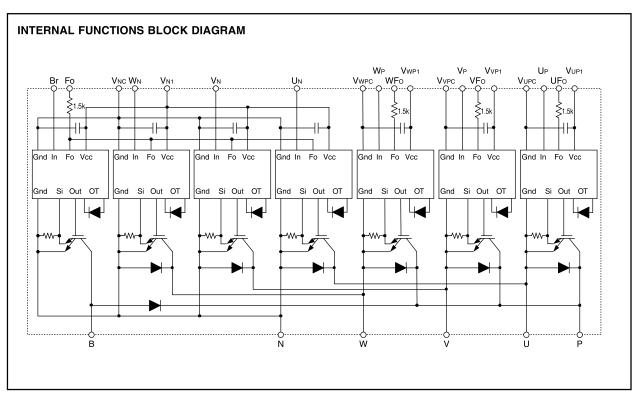
General purpose inverter, servo drives and other motor controls





May 2009

FLAT-BASE TYPE INSULATED PACKAGE



MAXIMUM RATINGS (Tj = 25° C, unless otherwise noted) **INVERTER PART**

Symbol	Parameter	Condition		Ratings	Unit
VCES	Collector-Emitter Voltage	VD = 15V, VCIN = 15V		600	V
±lc	Collector Current	$Tc = 25^{\circ}C $ (I	Note-1)	50	А
±ICP	Collector Current (Peak)	Tc = 25°C		100	Α
Pc	Collector Dissipation	$Tc = 25^{\circ}C$ (I	Note-1)	284	W
Tj	Junction Temperature			-20 ~ +150	°C

*: Tc measurement point is just under the chip.

BRAKE PART

Symbol	Parameter	Condition		Ratings	Unit
VCES	Collector-Emitter Voltage	VD = 15V, VCIN = 15V		600	V
lc	Collector Current	Tc = 25°C	(Note-1)	50	A
ICP	Collector Current (Peak)	Tc = 25°C		100	A
Pc	Collector Dissipation	Tc = 25°C	(Note-1)	284	W
lF	FWDi Forward Current	Tc = 25°C		50	A
VR(DC)	FWDi Rated DC Reverse Voltage	Tc = 25°C		600	V
Tj	Junction Temperature			-20 ~ +150	°C

CONTROL PART

Symbol	Parameter	Condition	Ratings	Unit
VD	Supply Voltage	Applied between : VUP1-VUPC, VVP1-VVPC	20	v
		VWP1-VWPC, VN1-VNC	20	v
VCIN	Input Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC	20	
VCIN		UN • VN • WN • Br-VNC	20	v
VFO		Applied between : UFO-VUPC, VFO-VVPC, WFO-VWPC	20	v
VFO	Fault Output Supply Voltage	Fo-Vnc	20	v
lfo	Fault Output Current	Sink current at UFO, VFO, WFO, FO terminals	20	mA



FLAT-BASE TYPE **INSULATED PACKAGE**

TOTAL SYSTEM

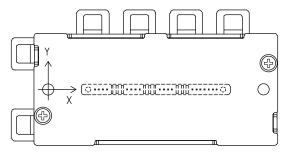
Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Supply Voltage Protected by SC	$V_D = 13.5 \sim 16.5V$ Inverter Part, Tj = +125°C Start	400	v
VCC(surge)	Supply Voltage (Surge)	Applied between : P-N, Surge value	500	V
Tstg	Storage Temperature		-40 ~ +125	°C
Viso	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base, AC 1 min.	2500	Vrms

THERMAL RESISTANCES

		Condition		Linit			
Symbol	Parameter	Condition		Min.	Тур.	Max.	Unit
Rth(j-c)Q		Inverter IGBT part (per 1 element)	(Note-1)			0.44	
Rth(j-c)F	Junction to case Thermal Resistances	Inverter FWDi part (per 1 element)	(Note-1)			0.75	
Rth(j-c)Q		Brake IGBT part	(Note-1)			0.44	°C/W
Rth(j-c)F		Brake FWDi upper part	(Note-1)			0.75	0/00
	Contact Thermal Resistance	Case to fin, (per 1 module)				0.000	
Rth(c-f)		Thermal grease applied	(Note-1)			0.038	

* If you use this value, Rth(f-a) should be measured just under the chips.

(Note-1) Tc (under the chip) measurement point is below. (unit : mn									it : mm)					
arm	U	Р	V	Р	N	/P	U	N	V	N	W	'N	В	R
axis	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	Di
Х	28.7	28.7	65.4	65.4	85.0	85.0	37.2	37.2	55.8	55.8	75.4	75.4	20.2	21.3
Y	-6.3	0.2	-6.3	0.2	-6.3	0.2	5.4	-0.9	5.4	-0.9	5.4	-0.9	-7.4	5.8



Bottom view

ELECTRICAL CHARACTERISTICS (Tj = 25° C, unless otherwise noted) **INVERTER PART**

		Condi	tion			Unit		
Symbol	Parameter	Condi	Condition			Тур.	Max.	
Vorum	Collector-Emitter Saturation	VD = 15V, IC = 50A		Tj = 25°C	_	1.75	2.35	v
VCE(sat)	Voltage	VCIN = 0V, Pulsed	(Fig. 1)	Tj = 125°C	—	1.75	2.35	v
VEC	FWDi Forward Voltage	-IC = 50A, VD = 15V, VCIN =	15V	(Fig. 2)	—	1.7	2.8	V
ton					0.3	0.8	2.0	
trr		$VD = 15V, VCIN = 0V \leftrightarrow 15V$			—	0.4	0.8	
tc(on)	Switching Time	VCC = 300V, IC = 50A			—	0.4	1.0	μs
toff		Tj = 125°C		(5	—	1.0	2.3	
tc(off)		Inductive Load		(Fig. 3,4)	—	0.3	1.0	
1050	Collector-Emitter Cutoff		([]	Tj = 25°C	—	—	1	
ICES	Current	VCE = VCES, VD = 15V	(Fig. 5)	Tj = 125°C	_	_	10	mA



FLAT-BASE TYPE INSULATED PACKAGE

BRAKE PART

O male al	Duranta	Condition			11		
Symbol	Symbol Parameter Condition			Min.	Тур.	Max.	Unit
	Collector-Emitter Saturation	VD = 15V, IC = 50A	Tj = 25°C	—	1.75	2.35	v
VCE(sat)	Voltage	VCIN = 0V, Pulsed (Fig. 1)	Tj = 125°C	—	1.75	2.35	v
VEC	FWDi Forward Voltage	−IC = 50A, VCIN = 15V, VD = 15V	(Fig. 2)	—	1.7	2.8	V
loco	Collector-Emitter Cutoff	VCE = VCES, VD = 15V (Fig. 5)	Tj = 25°C	—	—	1	
ICES	Current	VCE = VCES, VD = 15V (Fig. 5)	Tj = 125°C	_	_	10	mA

CONTROL PART

Currente e l	Demonster	Quantitian			Limits		11.1
Symbol	Parameter	Condition		Min.	Тур.	Max.	Unit
D	Circuit Current	VD = 15V, VCIN = 15V	VN1-VNC	—	8	16	m 1
			V*P1-V*PC	—	2	4	mA
Vth(ON)	Input ON Threshold Voltage	Applied between : UP-VUPC, VP-VVPC, V	WP-VWPC	1.2	1.5	1.8	v
Vth(OFF)	Input OFF Threshold Voltage	UN • VN • WN • Br-VN	1C	1.7	2.0	2.3	v
SC	Short Circuit Trip Level	$ -20 \le 1i \le 125^{\circ}C$, VD = 15V (Fig. 3.6) \vdash	Inverter part	100	—	_	A
30	Short Circuit Thp Level		Brake part	100	—		~
toff(SC)	Short Circuit Current Delay Time	VD = 15V	(Fig. 3,6)	_	0.2	_	μs
от	Over Temperature Protection	Detect Temperature of IGBT chip	Trip level	135	—		°C
OT(hys)			Hysteresis	_	20	_	
UV	Supply Circuit Under-Voltage	–20 ≤ Ti ≤ 125°C	Trip level	11.5	12.0	12.5	v
UVr	Protection	-20 ≤ 1j ≤ 125 C	Reset level	_	12.5		v
IFO(H)	Fault Output Current	VD = 15V, VCIN = 15V	(Note-2)	_	—	0.01	mA
IFO(L)			(10018-2)	_	10	15	
tFO	Minimum Fault Output Pulse Width	VD = 15V	(Note-2)	1.0	1.8	_	ms

(Note-2) Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

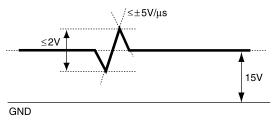
MECHANICAL RATINGS AND CHARACTERISTICS

	Duranta	Condition			Unit		
Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit	
—	Mounting torque	Mounting part	screw : M5	2.5	3.0	3.5	N•m
—	Mounting torque	Main terminal part	screw : M5	2.5	3.0	3.5	N•m
—	Weight	_		—	380	_	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Condition	Recommended value	Unit
Vcc	Supply Voltage	Applied across P-N terminals	≤ 400	V
VD	Control Supply Voltage	Applied between : VUP1-VUPC, VVP1-VVPC VWP1-VWPC, VN1-VNC (Note-3)	15.0 ± 1.5	v
VCIN(ON)	Input ON Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC	≤ 0.8	v
VCIN(OFF)	Input OFF Voltage	UN • VN • WN • Br-VNC	≥ 9.0	v
fpwм	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
tdead	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 2.0	μs

(Note-3) With ripple satisfying the following conditions: dv/dt swing $\leq \pm 5V/\mu s$, Variation $\leq 2V$ peak to peak



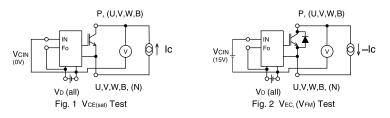


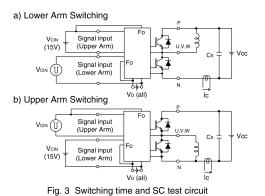
FLAT-BASE TYPE INSULATED PACKAGE

PRECAUTIONS FOR TESTING

- Before applying any control supply voltage (VD), the input terminals should be pulled up by resistors, etc. to their corresponding supply voltage and each input signal should be kept off state.
- After this, the specified ON and OFF level setting for each input signal should be done.
- 2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above VCEs rating of the device.

(These test should not be done by using a curve tracer or its equivalent.)





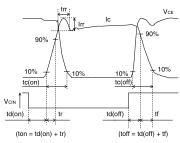
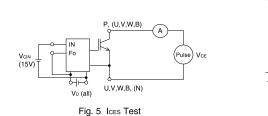
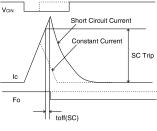
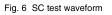
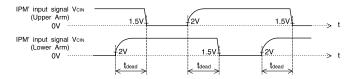


Fig. 4 Switching time test waveform









1.5V: Input on threshold voltage Vth(on) typical value, 2V: Input off threshold voltage Vth(off) typical value

Fig. 7 Dead time measurement point example



FLAT-BASE TYPE INSULATED PACKAGE

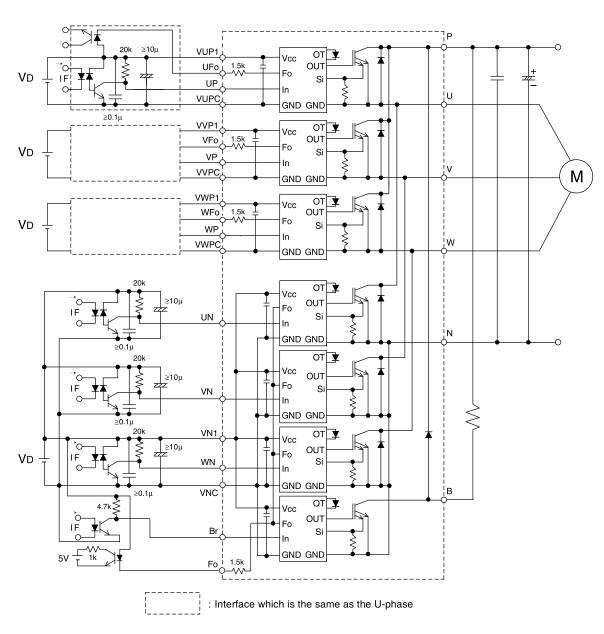


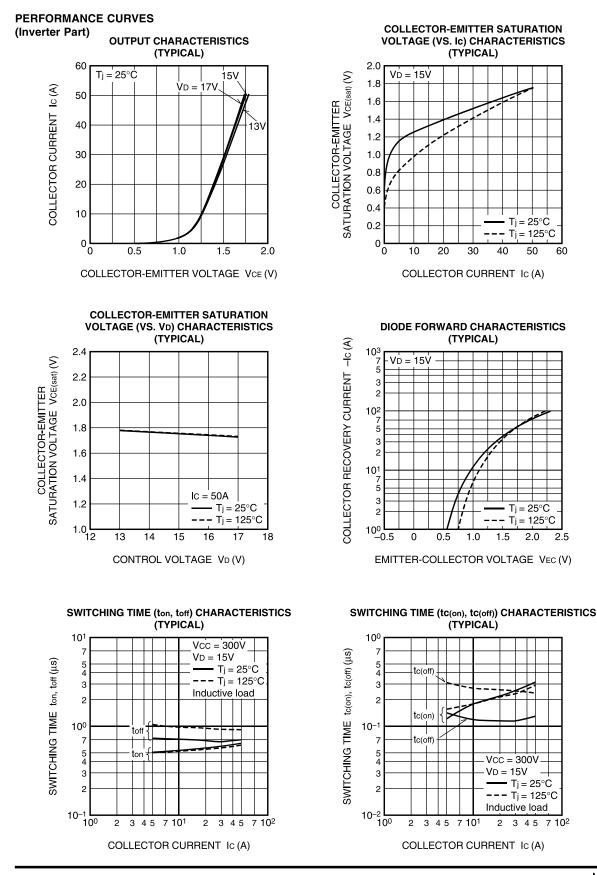
Fig. 8 Application Example Circuit

NOTES FOR STABLE AND SAFE OPERATION ;

- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- •Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: tPLH, tPHL \leq 0.8µs, Use High CMR type.
- •Slow switching opto-coupler: CTR > 100%
- •Use 4 isolated control power supplies (VD). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- •Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.
- •Use line noise filter capacitor (ex. 4.7nF) between each input AC line and ground to reject common-mode noise from AC line and improve noise immunity of the system.

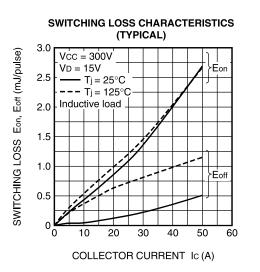


FLAT-BASE TYPE INSULATED PACKAGE

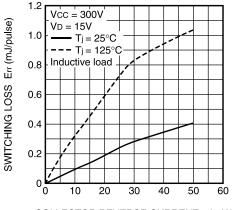




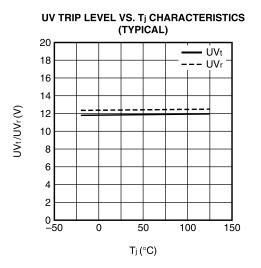
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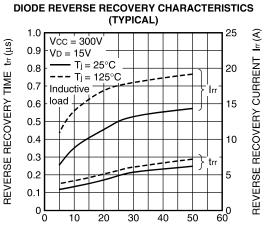


SWITCHING RECOVERY LOSS CHARACTERISTICS (TYPICAL)



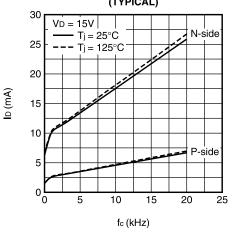
COLLECTOR REVERSE CURRENT -Ic (A)



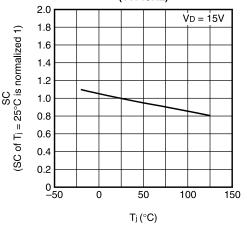


COLLECTOR REVERSE CURRENT -Ic (A)

ID VS. fc CHARACTERISTICS (TYPICAL)

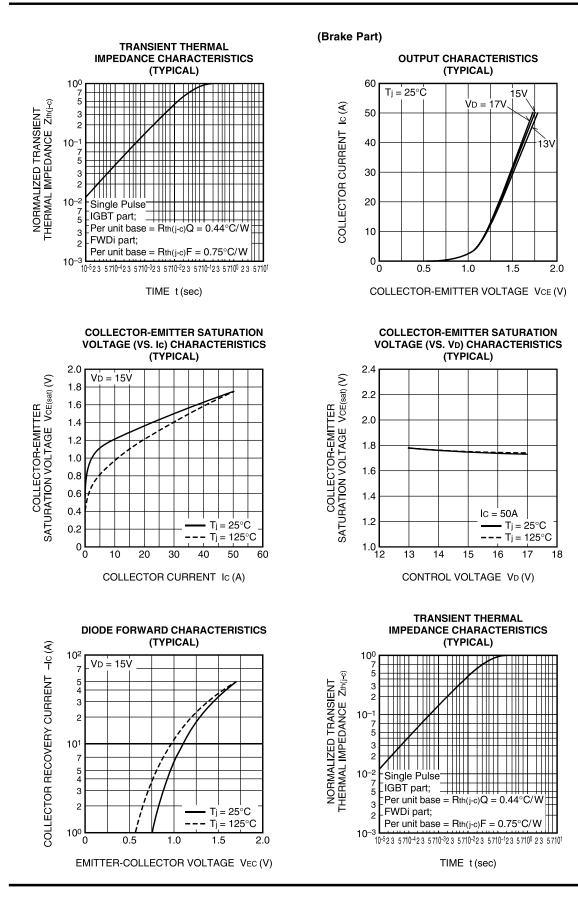


SC TRIP LEVEL VS. Tj CHARACTERISTICS (TYPICAL)





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